

Silicon PNP Power Transistors

2SB697 2SB697K

DESCRIPTION

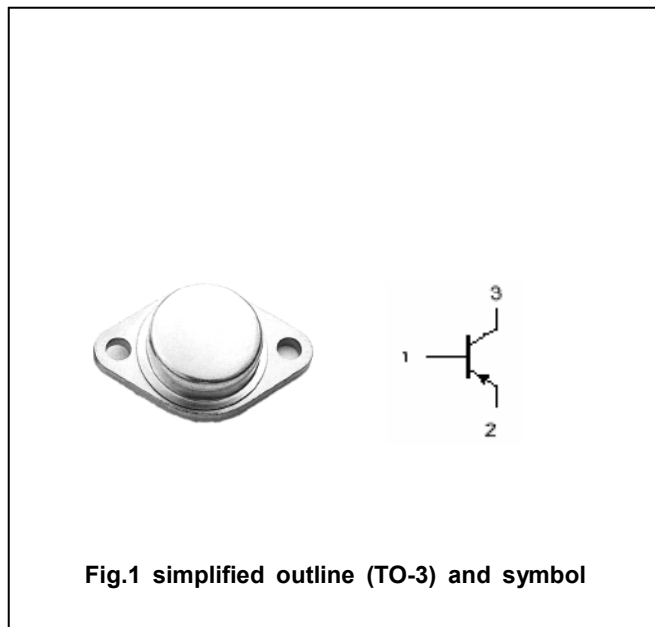
- With TO-3 package
- Complement to type 2SD733/733K
- High power dissipation

APPLICATIONS

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SB697	-160	V
		2SB697K	-180	
V _{CEO}	Collector-emitter voltage	2SB697	-140	V
		2SB697K	-160	
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-12	A
I _{CM}	Collector current-peak		-20	A
P _C	Collector power dissipation	T _C =25□	100	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-40~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SB697	I _C =-50mA ; I _B =0	-140			V
		2SB697K		-160			
V _{(BR)CBO}	Collector-emitter breakdown voltage	2SB697	I _C =-5mA ; I _E =0	-160			V
		2SB697K		-180			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-5mA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-6A ; I _B =-0.6A		-1.0	-2.5	V
V _{BE}	Base-emitter on voltage		I _C =-1A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =-80V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current		V _{EB} =-4V ; I _C =0			-0.1	mA
h _{FE-1}	DC current gain		I _C =-1A ; V _{CE} =-5V	40		320	
h _{FE-2}	DC current gain		I _C =-5A ; V _{CE} =-5V	20			
f _T	Transition frequency		I _C =-1A ; V _{CE} =-5V		15		MHz

◆ h_{FE-1} Classifications

C	D	E	F
40-80	60-120	100-200	160-320

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)